MC34071,2,4,A
MC33071,2,4,A

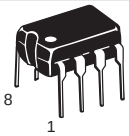
High Slew Rate, Wide Bandwidth, Single Supply Operational Amplifiers

Quality bipolar fabrication with innovative design concepts are employed for the MC33071/72/74, MC34071/72/74 series of monolithic operational amplifiers. This series of operational amplifiers offer 4.5 MHz of gain bandwidth product, 13 V/μs slew rate and fast setting time without the use of JFET device technology. Although this series can be operated from split supplies, it is particularly suited for single supply operation, since the common mode input voltage range includes ground potential (V_{EE}). With A Darlington input stage, this series exhibits high input resistance, low input offset voltage and high gain. The all NPN output stage, characterized by no deadband crossover distortion and large output voltage swing, provides high capacitance drive capability, excellent phase and gain margins, low open loop high frequency output impedance and symmetrical source/sink AC frequency response.

The MC33071/72/74, MC34071/72/74 series of devices are available in standard or prime performance (A Suffix) grades and are specified over the commercial, industrial/vehicular or military temperature ranges. The complete series of single, dual and quad operational amplifiers are available in plastic DIP, SOIC and TSSOP surface mount packages.

- Wide Bandwidth: 4.5 MHz
- High Slew Rate: 13 V/μs
- Fast Settling Time: 1.1 μs to 0.1%
- Wide Single Supply Operation: 3.0 V to 44 V
- Wide Input Common Mode Voltage Range: Includes Ground (V_{EE})
- Low Input Offset Voltage: 3.0 mV Maximum (A Suffix)
- Large Output Voltage Swing: –14.7 V to +14 V (with ±15 V Supplies)
- Large Capacitance Drive Capability: 0 pF to 10,000 pF
- Low Total Harmonic Distortion: 0.02%
- Excellent Phase Margin: 60°
- Excellent Gain Margin: 12 dB
- Output Short Circuit Protection
- ESD Diodes/Clamps Provide Input Protection for Dual and Quad

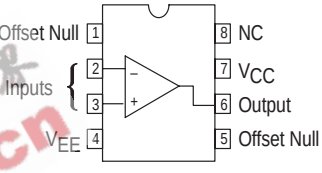
ON Semiconductor
Formerly a Division of Motorola
http://onsemi.com



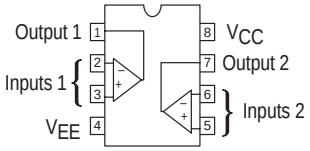
P SUFFIX
CASE 626

SO–8
D SUFFIX
CASE 751

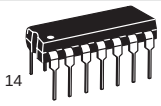
PIN CONNECTIONS



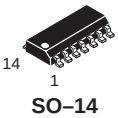
(Single, Top View)



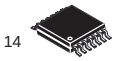
(Dual, Top View)



P SUFFIX
CASE 646

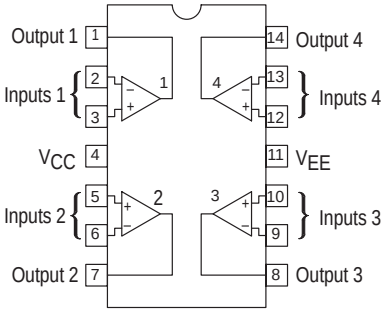


SO–14
D SUFFIX
CASE 751A



TSSOP–14
DTB SUFFIX
CASE 948G

PIN CONNECTIONS

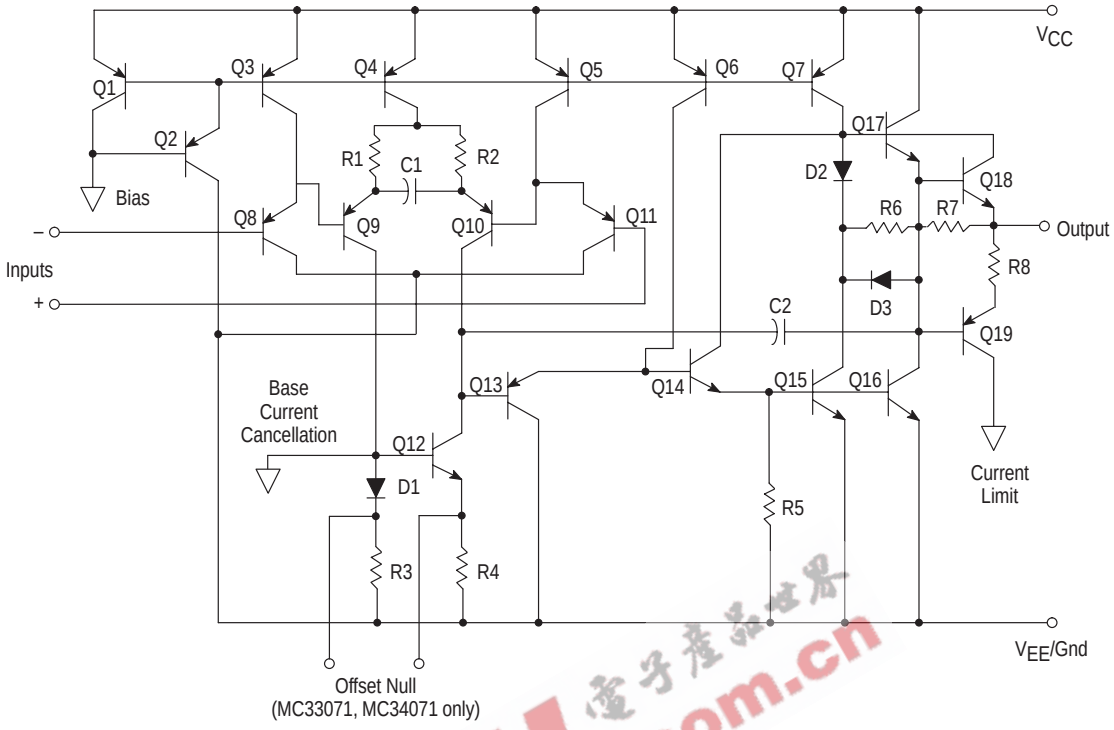


(Quad, Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 17 of this data sheet.

Representative Schematic Diagram
(Each Amplifier)



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage (from V_{EE} to V_{CC})	V_S	+44	V
Input Differential Voltage Range	V_{IDR}	Note 1	V
Input Voltage Range	V_{IR}	Note 1	V
Output Short Circuit Duration (Note 2)	t_{SC}	Indefinite	sec
Operating Junction Temperature	T_J	+150	°C
Storage Temperature Range	T_{stg}	–60 to +150	°C

NOTES: 1. Either or both input voltages should not exceed the magnitude of V_{CC} or V_{EE}.
2. Power dissipation must be considered to ensure maximum junction temperature (T_J) is not exceeded (see Figure 1).

ELECTRICAL CHARACTERISTICS (V_{CC} = +15 V, V_{EE} = –15 V, R_L = connected to ground, unless otherwise noted. See Note 3 for T_A = T_{low} to T_{high})

Characteristics	Symbol	A Suffix			Non–Suffix			Unit
		Min	Typ	Max	Min	Typ	Max	
Input Offset Voltage (R_S = 100 Ω, V_{CM} = 0 V, V_O = 0 V) V_{CC} = +15 V, V_{EE} = –15 V, T_A = +25°C V_{CC} = +5.0 V, V_{EE} = 0 V, T_A = +25°C V_{CC} = +15 V, V_{EE} = –15 V, T_A = T_{low} to T_{high}	V_{IO}	 — — —	 0.5 0.5 —	 3.0 3.0 5.0	 — — —	 1.0 1.5 —	 5.0 5.0 7.0	mV
Average Temperature Coefficient of Input Offset Voltage R_S = 10 Ω, V_{CM} = 0 V, V_O = 0 V, T_A = T_{low} to T_{high}	$\Delta V_{IO}/\Delta T$	—	10	—	—	10	—	μV/°C
Input Bias Current (V_{CM} = 0 V, V_O = 0 V) T_A = +25°C T_A = T_{low} to T_{high}	I_{IB}	 — —	 100 —	 500 700	 — —	 100 —	 500 700	nA
Input Offset Current (V_{CM} = 0 V, V_O = 0V) T_A = +25°C T_A = T_{low} to T_{high}	I_{IO}	 — —	 6.0 —	 50 300	 — —	 6.0 —	 75 300	nA
Input Common Mode Voltage Range T_A = +25°C T_A = T_{low} to T_{high}	V_{ICR}	V_{EE} to (V_{CC} –1.8) V_{EE} to (V_{CC} –2.2)			V_{EE} to (V_{CC} –1.8) V_{EE} to (V_{CC} –2.2)			V
Large Signal Voltage Gain (V_O = ±10 V, R_L = 2.0 kΩ) T_A = +25°C T_A = T_{low} to T_{high}	A_{VOL}	 50 25	 100 —	 — —	 25 20	 100 —	 — —	V/mV
Output Voltage Swing (V_{ID} = ±1.0 V) V_{CC} = +5.0 V, V_{EE} = 0 V, R_L = 2.0 kΩ, T_A = +25°C V_{CC} = +15 V, V_{EE} = –15 V, R_L = 10 kΩ, T_A = +25°C V_{CC} = +15 V, V_{EE} = –15 V, R_L = 2.0 kΩ, T_A = T_{low} to T_{high}	V_{OH}	 3.7 13.6 13.4	 4.0 14 —	 — — —	 3.7 13.6 13.4	 4.0 14 —	 — — —	V
V_{CC} = +5.0 V, V_{EE} = 0 V, R_L = 2.0 kΩ, T_A = +25°C V_{CC} = +15 V, V_{EE} = –15 V, R_L = 10 kΩ, T_A = +25°C V_{CC} = +15 V, V_{EE} = –15 V, R_L = 2.0 kΩ, T_A = T_{low} to T_{high}	V_{OL}	 — — —	 0.1 –14.7 —	 0.3 –14.3 –13.5	 — — —	 0.1 –14.7 —	 0.3 –14.3 –13.5	V
Output Short Circuit Current (V_{ID} = 1.0 V, V_O = 0 V, T_A = 25°C) Source Sink	I_{SC}	 10 20	 30 30	 — —	 10 20	 30 30	 — —	mA
Common Mode Rejection R_S ≤ 10 kΩ, V_{CM} = V_{ICR}, T_A = 25°C	CMR	80	97	—	70	97	—	dB
Power Supply Rejection (R_S = 100 Ω) V_{CC}/V_{EE} = +16.5 V/–16.5 V to +13.5 V/–13.5 V, T_A = 25°C	PSR	80	97	—	70	97	—	dB
Power Supply Current (Per Amplifier, No Load) V_{CC} = +5.0 V, V_{EE} = 0 V, V_O = +2.5 V, T_A = +25°C V_{CC} = +15 V, V_{EE} = –15 V, V_O = 0 V, T_A = +25°C V_{CC} = +15 V, V_{EE} = –15 V, V_O = 0 V, T_A = T_{low} to T_{high}	I_D	 — — —	 1.6 1.9 —	 2.0 2.5 2.8	 — — —	 1.6 1.9 —	 2.0 2.5 2.8	mA

NOTES: 3. T_{low} = –40°C for MC33071, 2, 4, /A
= 0°C for MC34071, 2, 4, /A
T_{high} = +85°C for MC33071, 2, 4, /A
= +70°C for MC34071, 2, 4, /A

AC ELECTRICAL CHARACTERISTICS (V_{CC} = +15 V, V_{EE} = –15 V, R_L = connected to ground. T_A = +25°C, unless otherwise noted.)

Characteristics	Symbol	A Suffix			Non–Suffix			Unit
		Min	Typ	Max	Min	Typ	Max	
Slew Rate (V_{in} = –10 V to +10 V, R_L = 2.0 kΩ, C_L = 500 pF) A_V = +1.0 A_V = –1.0	SR	 8.0 —	 10 13	 — —	 8.0 —	 10 13	 — —	V/μs
Setting Time (10 V Step, A_V = –1.0) To 0.1% (+1/2 LSB of 9–Bits) To 0.01% (+1/2 LSB of 12–Bits)	t_s	 — —	 1.1 2.2	 — —	 — —	 1.1 2.2	 — —	μs
Gain Bandwidth Product (f = 100 kHz)	GBW	3.5	4.5	—	3.5	4.5	—	MHz
Power Bandwidth A_V = +1.0, R_L = 2.0 kΩ, V_O = 20 V_{pp}, THD = 5.0%	BW	—	160	—	—	160	—	kHz
Phase margin R_L = 2.0 kΩ R_L = 2.0 kΩ, C_L = 300 pF	f_m	 — —	 60 40	 — —	 — —	 60 40	 — —	Deg
Gain Margin R_L = 2.0 kΩ R_L = 2.0 kΩ, C_L = 300 pF	A_m	 — —	 12 4.0	 — —	 — —	 12 4.0	 — —	dB
Equivalent Input Noise Voltage R_S = 100 Ω, f = 1.0 kHz	e_n	—	32	—	—	32	—	nV/√Hz
Equivalent Input Noise Current f = 1.0 kHz	i_n	—	0.22	—	—	0.22	—	pA/√Hz
Differential Input Resistance V_{CM} = 0 V	R_{in}	—	150	—	—	150	—	MΩ
Differential Input Capacitance V_{CM} = 0 V	C_{in}	—	2.5	—	—	2.5	—	pF
Total Harmonic Distortion A_V = +10, R_L = 2.0 kΩ, 2.0 $V_{pp} \le V_O \le$ 20 V_{pp}, f = 10 kHz	THD	—	0.02	—	—	0.02	—	%
Channel Separation (f = 10 kHz)	—	—	120	—	—	120	—	dB
Open Loop Output Impedance (f = 1.0 MHz)	$\|Z_O\|$	—	30	—	—	30	—	W

Figure 1. Power Supply Configurations

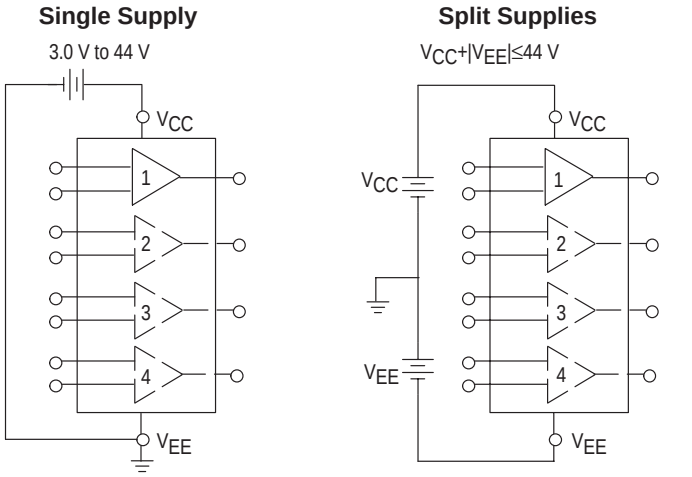
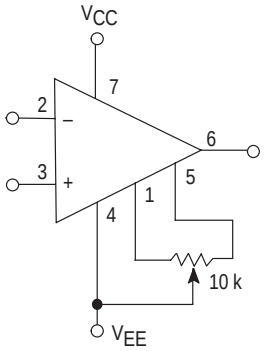


Figure 2. Offset Null Circuit



Offset nulling range is approximately ±80 mV with a 10 k potentiometer (MC33071, MC34071 only).

Figure 3. Maximum Power Dissipation versus Temperature for Package Types

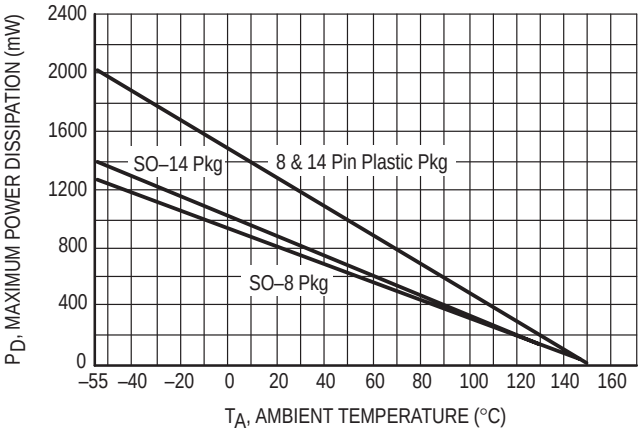


Figure 4. Input Offset Voltage versus Temperature for Representative Units

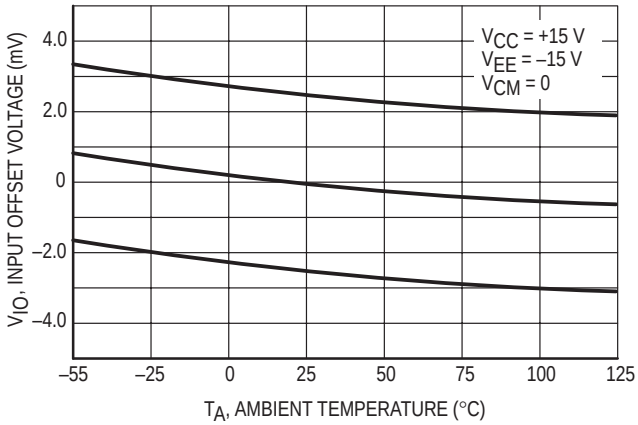


Figure 5. Input Common Mode Voltage Range versus Temperature

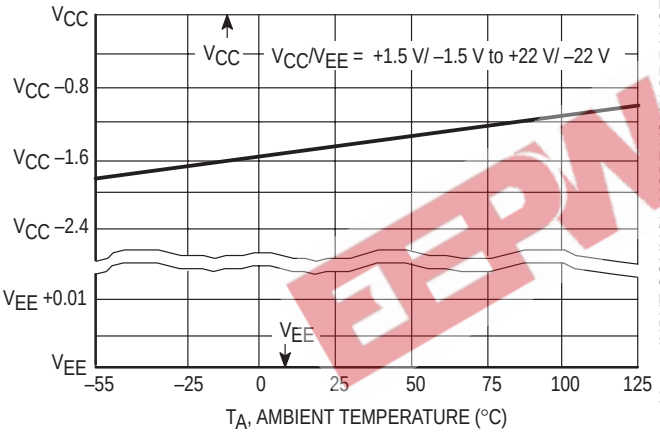


Figure 6. Normalized Input Bias Current versus Temperature

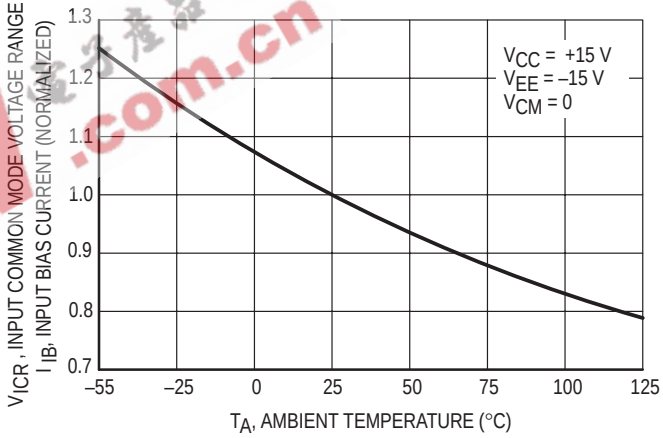


Figure 7. Normalized Input Bias Current versus Input Common Mode Voltage

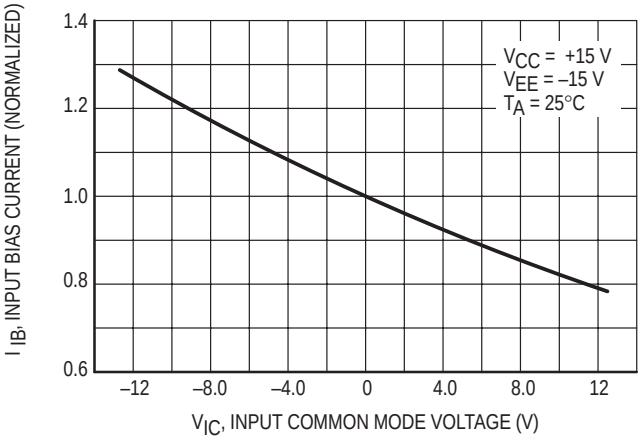


Figure 8. Split Supply Output Voltage Swing versus Supply Voltage

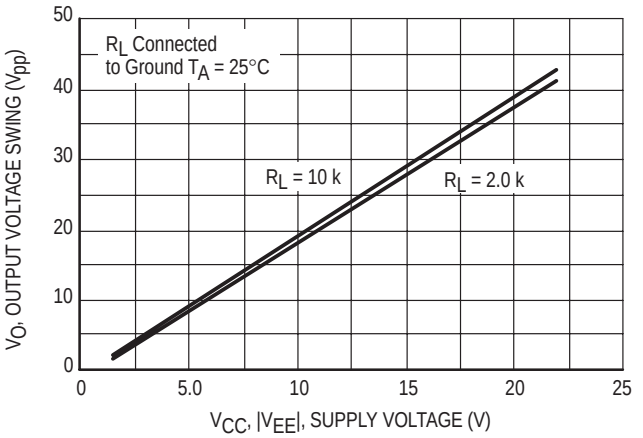


Figure 9. Single Supply Output Saturation versus Load Resistance to V_{CC}

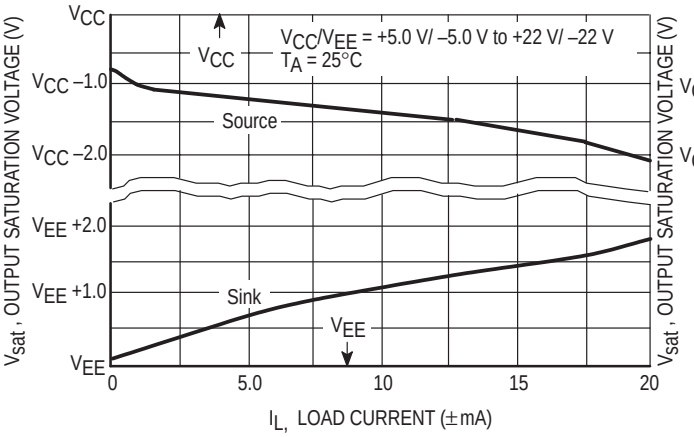


Figure 10. Split Supply Output Saturation versus Load Current

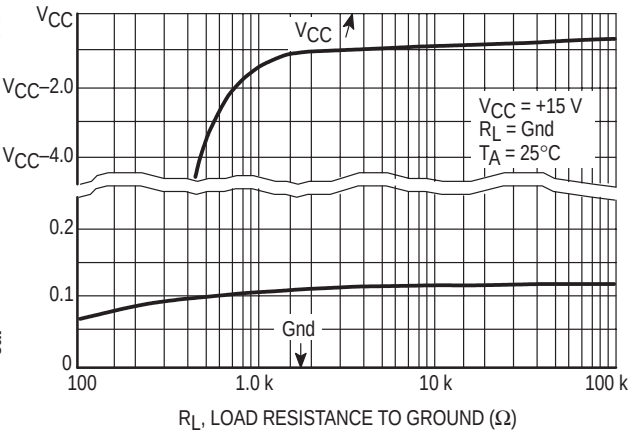


Figure 11. Single Supply Output Saturation versus Load Resistance to Ground

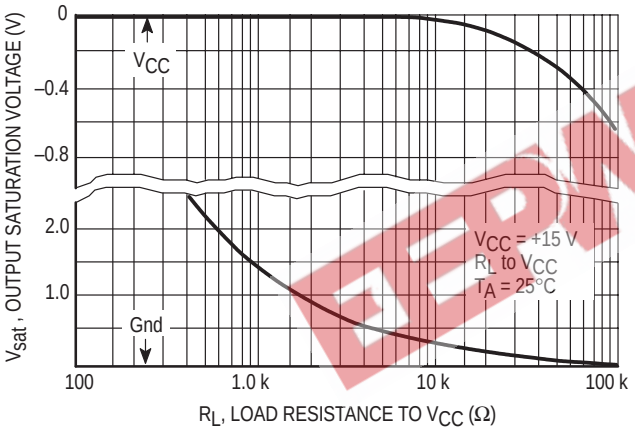


Figure 12. Output Short Circuit Current versus Temperature

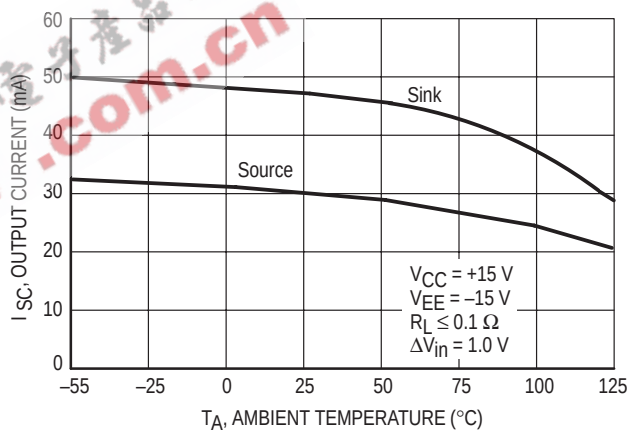


Figure 13. Output Impedance versus Frequency

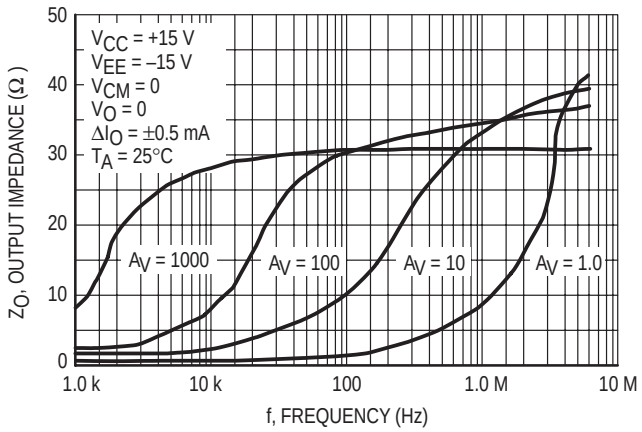


Figure 14. Output Voltage Swing versus Frequency

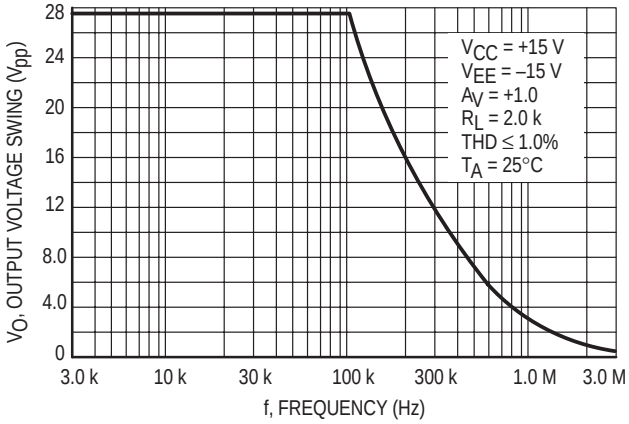


Figure 15. Total Harmonic Distortion versus Frequency

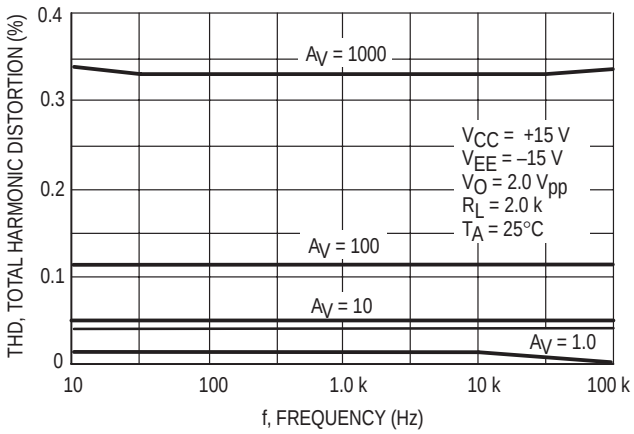


Figure 16. Total Harmonic Distortion versus Output Voltage Swing

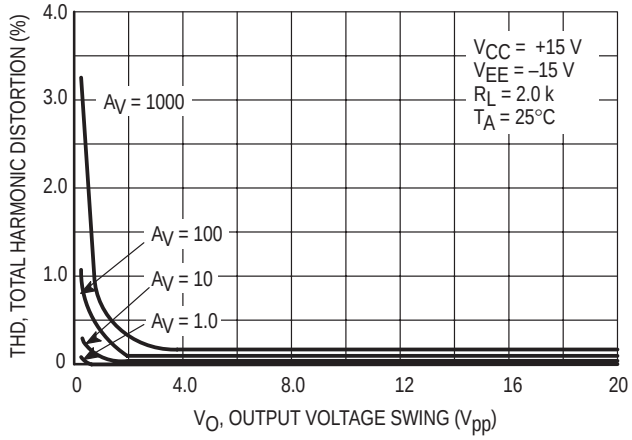


Figure 17. Open Loop Voltage Gain versus Temperature

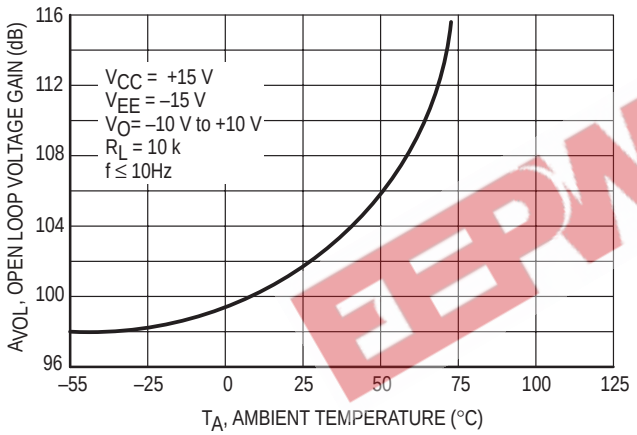


Figure 18. Open Loop Voltage Gain and Phase versus Frequency

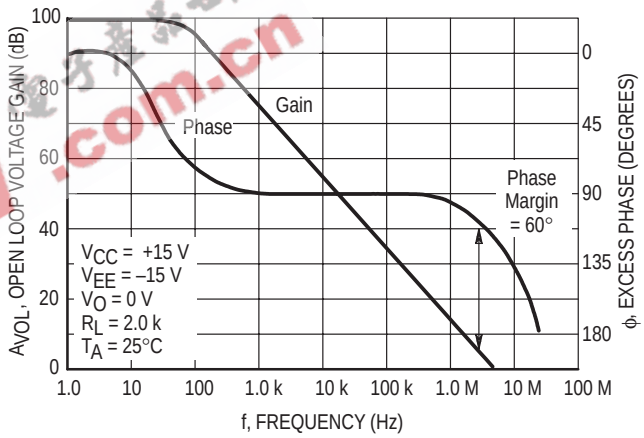


Figure 19. Open Loop Voltage Gain and Phase versus Frequency

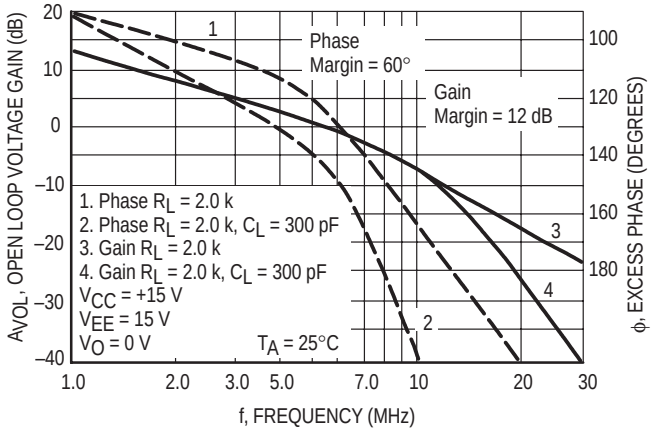


Figure 20. Normalized Gain Bandwidth Product versus Temperature

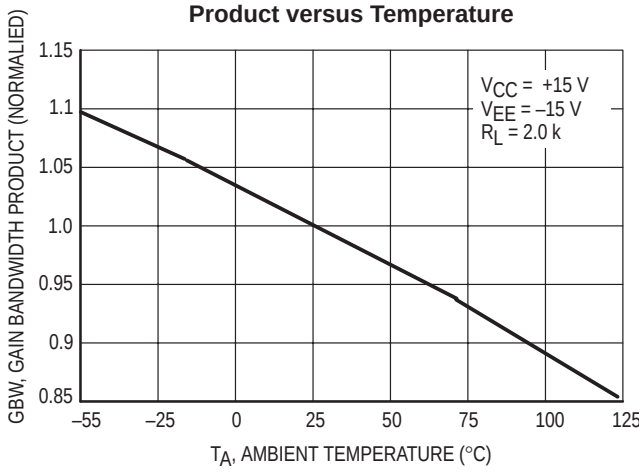


Figure 21. Percent Overshoot versus Load Capacitance

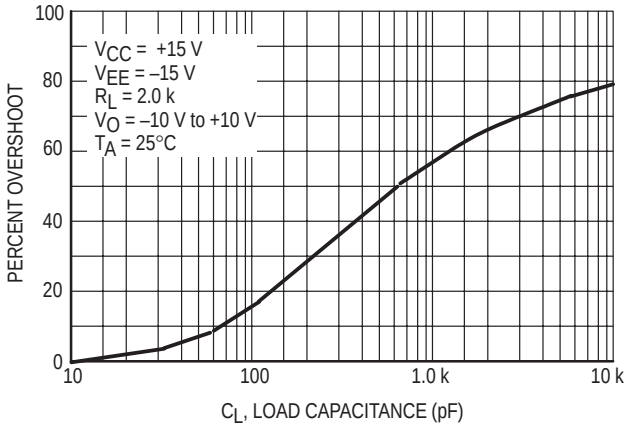


Figure 22. Phase Margin versus Load Capacitance

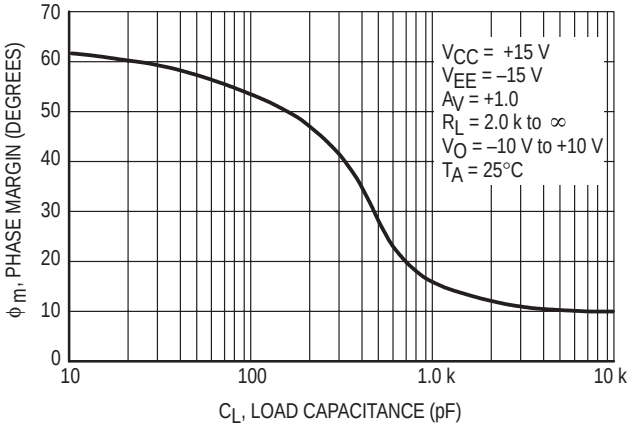


Figure 23. Gain Margin versus Load Capacitance

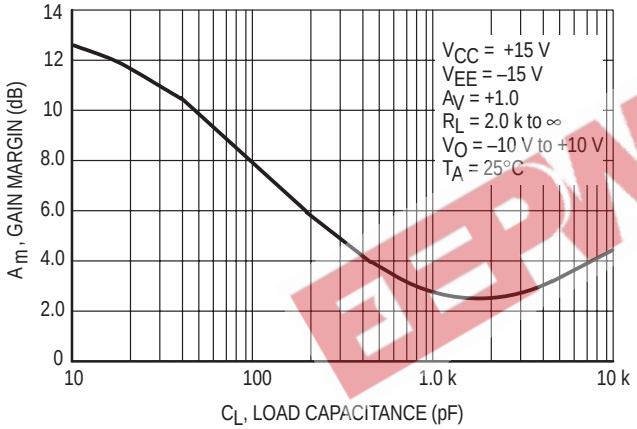


Figure 24. Phase Margin versus Temperature

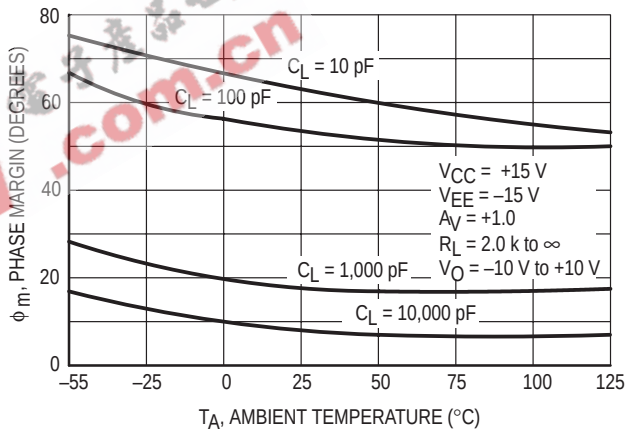


Figure 25. Gain Margin versus Temperature

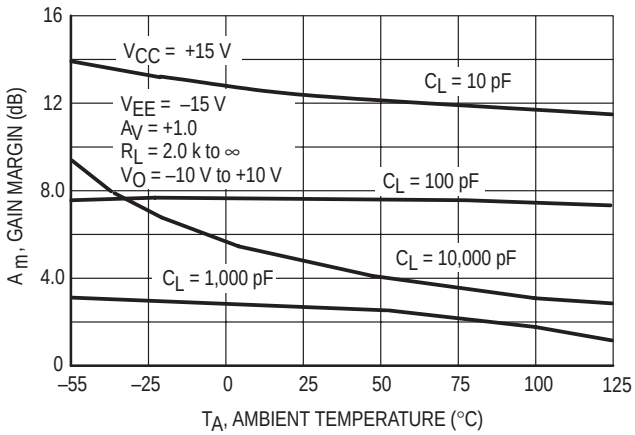


Figure 26. Phase Margin and Gain Margin versus Differential Source Resistance

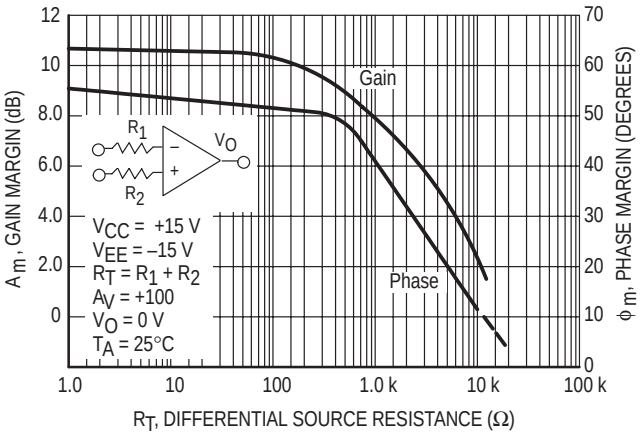


Figure 27. Normalized Slew Rate versus Temperature

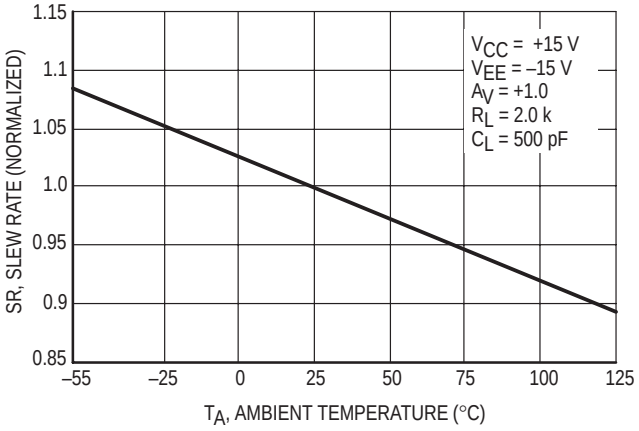


Figure 28. Output Settling Time

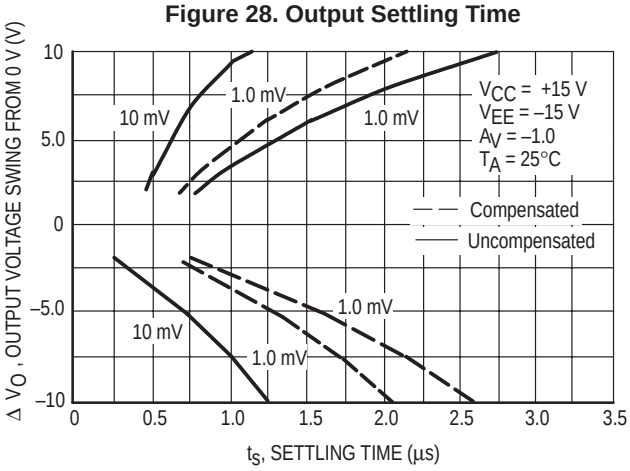


Figure 29. Small Signal Transient Response

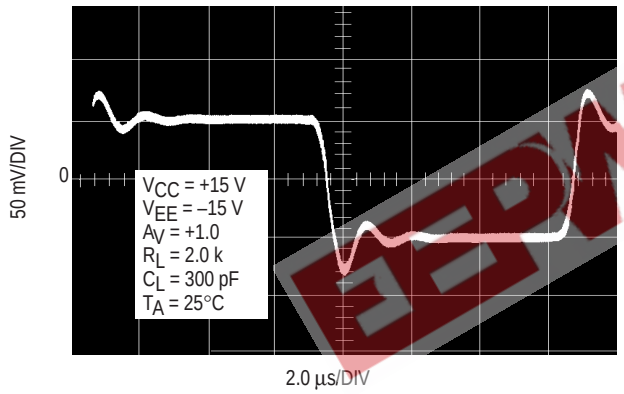


Figure 30. Large Signal Transient Reponse

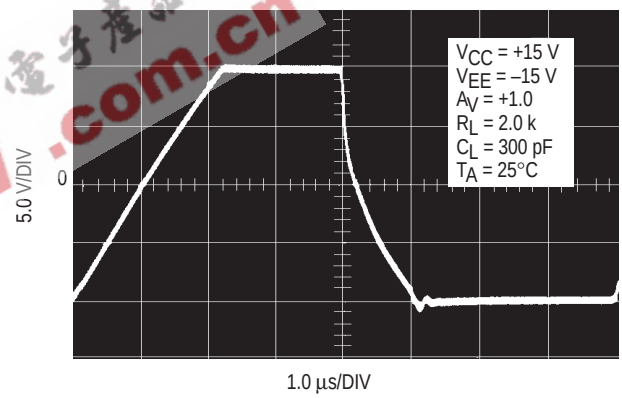


Figure 31. Common Mode Rejection versus Frequency

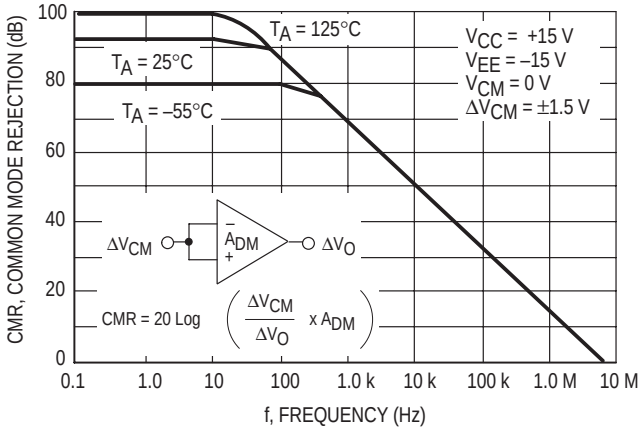


Figure 32. Power Supply Rejection versus Frequency

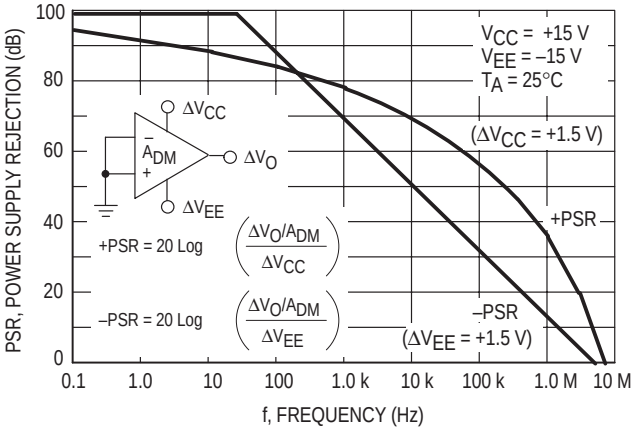


Figure 33. Supply Current versus Supply Voltage

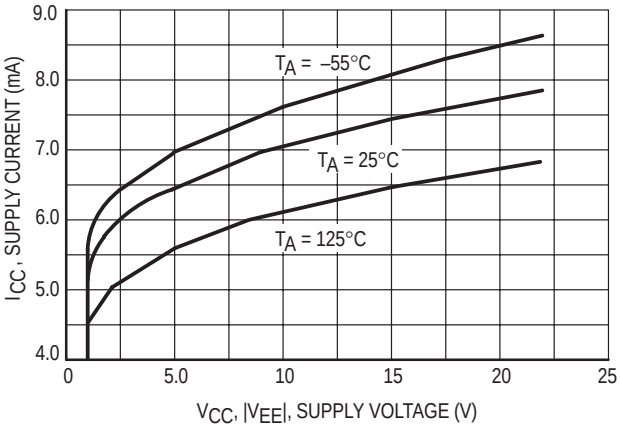


Figure 34. Power Supply Rejection versus Temperature

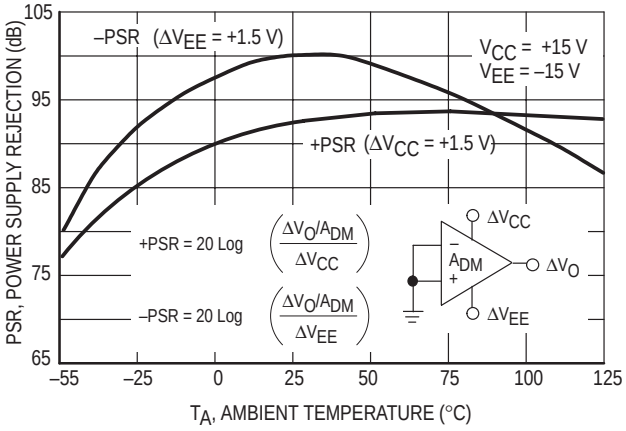


Figure 35. Channel Separation versus Frequency

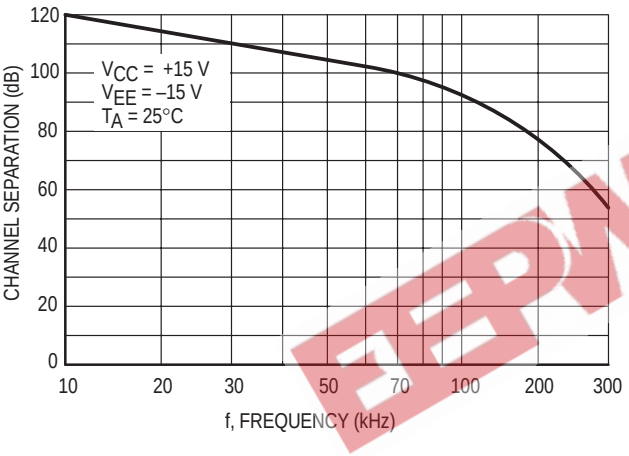
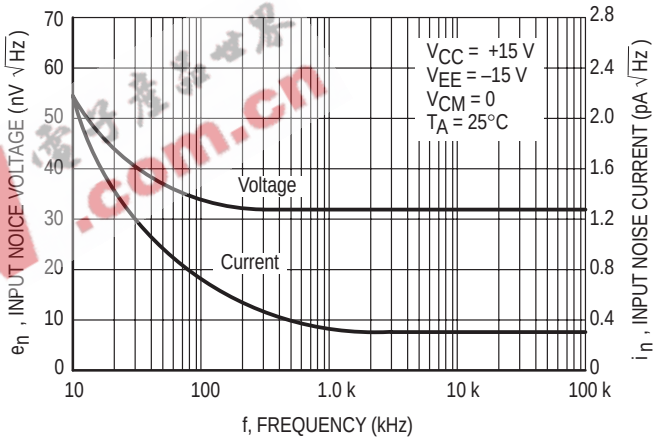


Figure 36. Input Noise versus Frequency



APPLICATIONS INFORMATION
CIRCUIT DESCRIPTION/PERFORMANCE FEATURES

Although the bandwidth, slew rate, and settling time of the MC34071 amplifier series are similar to op amp products utilizing JFET input devices, these amplifiers offer other additional distinct advantages as a result of the PNP transistor differential input stage and an all NPN transistor output stage.

Since the input common mode voltage range of this input stage includes the V_{EE} potential, single supply operation is feasible to as low as 3.0 V with the common mode input voltage at ground potential.

The input stage also allows differential input voltages up to ±44 V, provided the maximum input voltage range is not exceeded. Specifically, the input voltages must range between V_{EE} and V_{CC} supply voltages as shown by the maximum rating table. In practice, although not recommended, the input voltages can exceed the V_{CC} voltage by approximately 3.0 V and decrease below the V_{EE} voltage by 0.3 V without causing product damage, although output phase reversal may occur. It is also possible to source up to approximately 5.0 mA of current from V_{EE} through either inputs clamping diode without damage or latching, although phase reversal may again occur.

If one or both inputs exceed the upper common mode voltage limit, the amplifier output is readily predictable and may be in a low or high state depending on the existing input bias conditions.

Since the input capacitance associated with the small geometry input device is substantially lower (2.5 pF) than the typical JFET input gate capacitance (5.0 pF), better frequency response for a given input source resistance can be achieved using the MC34071 series of amplifiers. This performance feature becomes evident, for example, in fast settling D–to–A current to voltage conversion applications where the feedback resistance can form an input pole with the input capacitance of the op amp. This input pole creates a 2nd order system with the single pole op amp and is therefore detrimental to its settling time. In this context, lower input capacitance is desirable especially for higher

values of feedback resistances (lower current DACs). This input pole can be compensated for by creating a feedback zero with a capacitance across the feedback resistance, if necessary, to reduce overshoot. For 2.0 kΩ of feedback resistance, the MC34071 series can settle to within 1/2 LSB of 8 bits in 1.0 μs, and within 1/2 LSB of 12–bits in 2.2 μs for a 10 V step. In a inverting unity gain fast settling configuration, the symmetrical slew rate is ±13 V/μs. In the classic noninverting unity gain configuration, the output positive slew rate is +10 V/μs, and the corresponding negative slew rate will exceed the positive slew rate as a function of the fall time of the input waveform.

Since the bipolar input device matching characteristics are superior to that of JFETs, a low untrimmed maximum offset voltage of 3.0 mV prime and 5.0 mV downgrade can be economically offered with high frequency performance characteristics. This combination is ideal for low cost precision, high speed quad op amp applications.

The all NPN output stage, shown in its basic form on the equivalent circuit schematic, offers unique advantages over the more conventional NPN/PNP transistor Class AB output stage. A 10 kΩ load resistance can swing within 1.0 V of the positive rail (V_{CC}), and within 0.3 V of the negative rail (V_{EE}), providing a 28.7 V_{pp} swing from ±15 V supplies. This large output swing becomes most noticeable at lower supply voltages.

The positive swing is limited by the saturation voltage of the current source transistor Q_7, and V_{BE} of the NPN pull up transistor Q_{17}, and the voltage drop associated with the short circuit resistance, R_7. The negative swing is limited by the saturation voltage of the pull–down transistor Q_{16}, the voltage drop $I_L R_6$, and the voltage drop associated with resistance R_7, where I_L is the sink load current. For small valued sink currents, the above voltage drops are negligible, allowing the negative swing voltage to approach within millivolts of V_{EE}. For large valued sink currents (>5.0 mA), diode D3 clamps the voltage across R_6, thus limiting the negative swing to the saturation voltage of Q_{16}, plus the forward diode drop of D3 (≈V_{EE} +1.0 V). Thus for a given supply voltage, unprecedented peak–to–peak output voltage swing is possible as indicated by the output swing specifications.

If the load resistance is referenced to V_{CC} instead of ground for single supply applications, the maximum possible output swing can be achieved for a given supply voltage. For light load currents, the load resistance will pull the output to V_{CC} during the positive swing and the output will pull the load resistance near ground during the negative swing. The load resistance value should be much less than that of the feedback resistance to maximize pull up capability.

Because the PNP output emitter–follower transistor has been eliminated, the MC34071 series offers a 20 mA minimum current sink capability, typically to an output voltage of (V_{EE} +1.8 V). In single supply applications the output can directly source or sink base current from a common emitter NPN transistor for fast high current switching applications.

In addition, the all NPN transistor output stage is inherently fast, contributing to the bipolar amplifier's high gain bandwidth product and fast settling capability. The associated high frequency low output impedance (30 Ω typ @ 1.0 MHz) allows capacitive drive capability from 0 pF to 10,000 pF without oscillation in the unity closed loop gain configuration. The 60° phase margin and 12 dB gain margin as well as the general gain and phase characteristics are virtually independent of the source/sink output swing conditions. This allows easier system phase compensation, since output swing will not be a phase consideration. The high frequency characteristics of the MC34071 series also allow excellent high frequency active filter capability, especially for low voltage single supply applications.

Although the single supply specifications is defined at 5.0 V, these amplifiers are functional to 3.0 V @ 25°C although slight changes in parametrics such as bandwidth, slew rate, and DC gain may occur.

If power to this integrated circuit is applied in reverse polarity or if the IC is installed backwards in a socket, large unlimited current surges will occur through the device that may result in device destruction.

Special static precautions are not necessary for these bipolar amplifiers since there are no MOS transistors on the die.

As with most high frequency amplifiers, proper lead dress, component placement, and PC board layout should be exercised for optimum frequency performance. For example, long unshielded input or output leads may result in unwanted input–output coupling. In order to preserve the relatively low input capacitance associated with these amplifiers, resistors connected to the inputs should be immediately adjacent to the input pin to minimize additional stray input capacitance. This not only minimizes the input pole for optimum frequency response, but also minimizes extraneous "pick up" at this node. Supply decoupling with adequate capacitance immediately adjacent to the supply pin is also important, particularly over temperature, since many types of decoupling capacitors exhibit great impedance changes over temperature.

The output of any one amplifier is current limited and thus protected from a direct short to ground. However, under such conditions, it is important not to allow the device to exceed the maximum junction temperature rating. Typically for ±15 V supplies, any one output can be shorted continuously to ground without exceeding the maximum temperature rating.

(Typical Single Supply Applications V_{CC} = 5.0 V)

Figure 37. AC Coupled Noninverting Amplifer

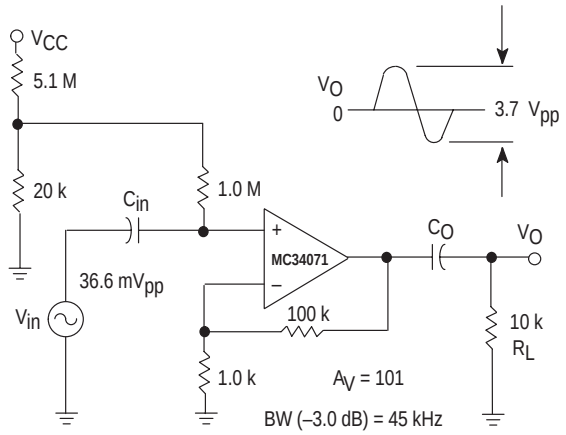


Figure 38. AC Coupled Inverting Amplifier

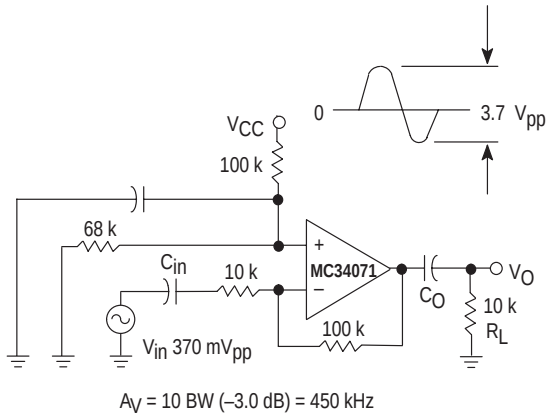


Figure 39. DC Coupled Inverting Amplifer Maximum Output Swing

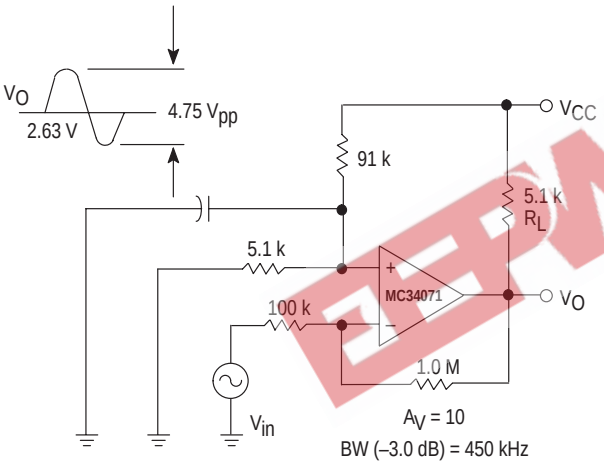


Figure 40. Unity Gain Buffer TTL Driver

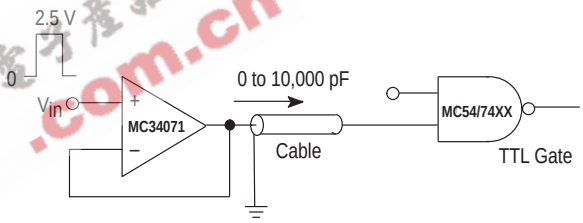


Figure 41. Active High–Q Notch Filter

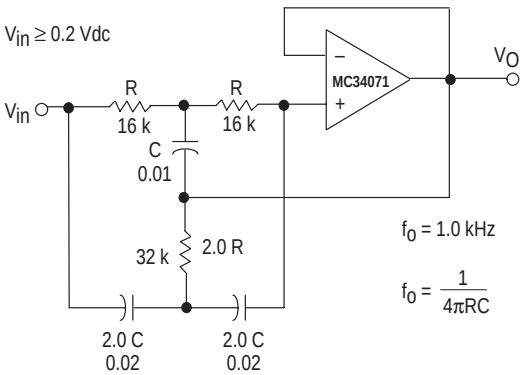
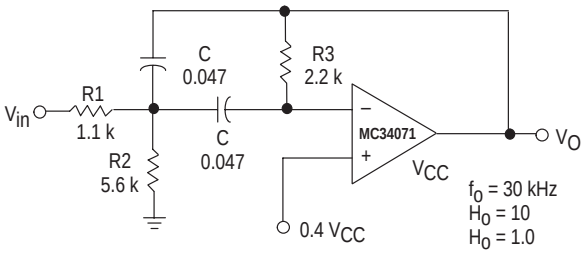


Figure 42. Active Bandpass Filter



Given f_0 = Center Frequency
A_O = Gain at Center Frequency
Choose Value f_0, Q, A_0, C

Then:

$$R3 = \frac{Q}{\pi f_0 C} \quad R1 = \frac{R3}{2H_0} \quad R2 = \frac{R1\,R3}{4Q^2R1 - R3}$$

For less than 10% error from operational amplifier $\frac{Q_0 f_0}{GBW} < 0.1$

where f_0 and GBW are expressed in Hz.
GBW = 4.5 MHz Typ.

Figure 43. Low Voltage Fast D/A Converter

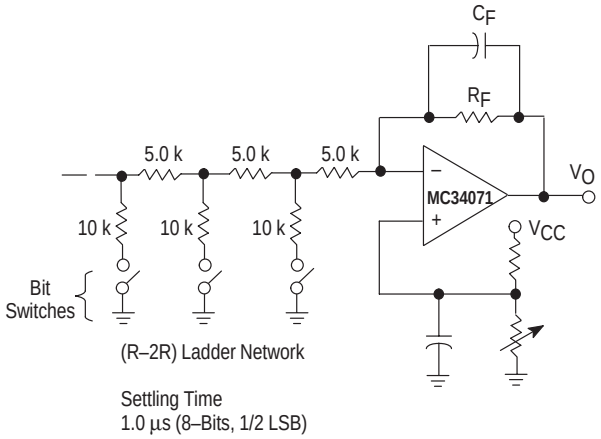


Figure 44. High Speed Low Voltage Comparator

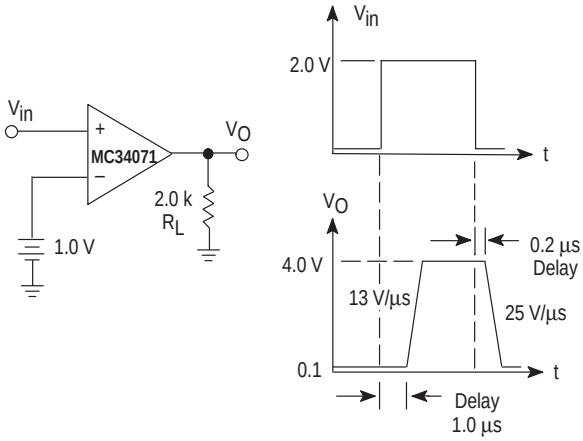


Figure 45. LED Driver

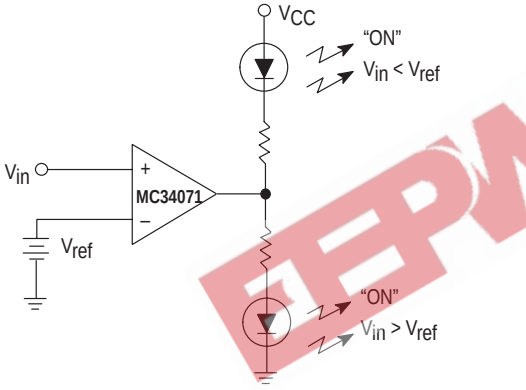


Figure 46. Transistor Driver

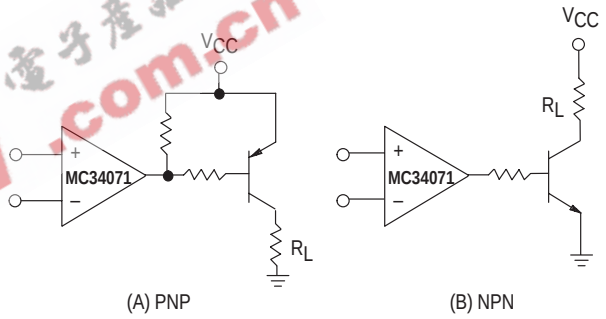


Figure 47. AC/DC Ground Current Monitor

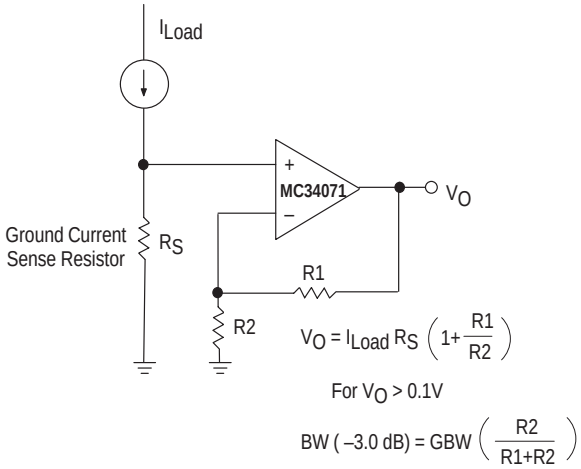


Figure 48. Photovoltaic Cell Amplifier

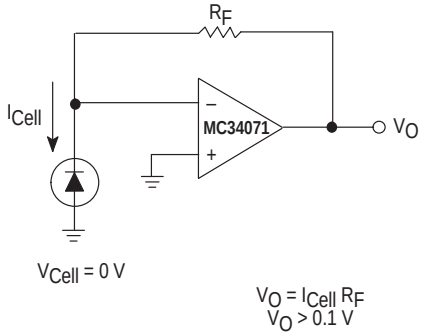
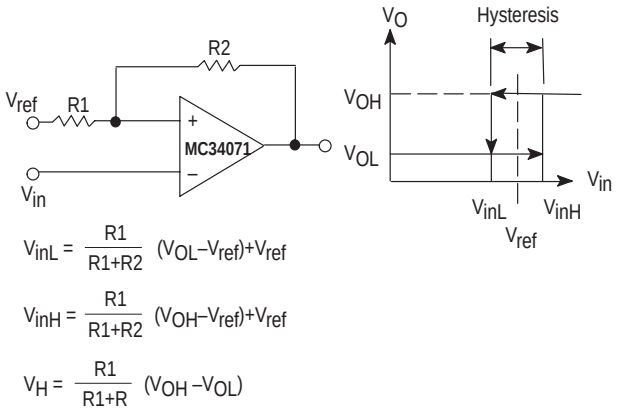


Figure 49. Low Input Voltage Comparator with Hysteresis



$$V_{inL} = \frac{R1}{R1+R2}(V_{OL}-V_{ref})+V_{ref}$$

$$V_{inH} = \frac{R1}{R1+R2}(V_{OH}-V_{ref})+V_{ref}$$

$$V_H = \frac{R1}{R1+R}(V_{OH}-V_{OL})$$

Figure 50. High Compliance Voltage to Sink Current Converter

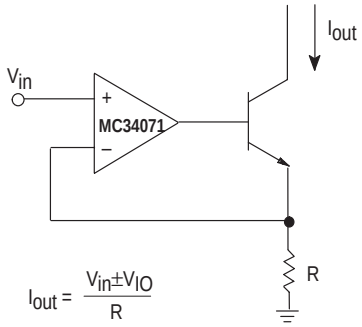
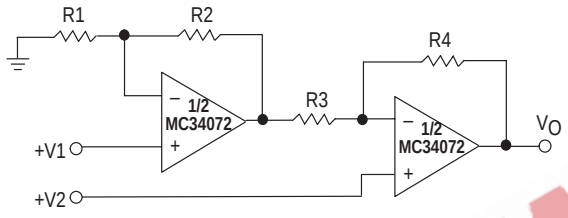


Figure 51. High Input Impedance Differential Amplifier



$$\frac{R2}{R1} = \frac{R4}{R3} \text{ (Critical to CMRR)}$$

$$V_O = 1\left(+\frac{R4}{R3}\right)\left(V2-V1\,\frac{R4}{R3}\right)$$

For (V2 ≥ V1), V > 0

Figure 52. Bridge Current Amplifier

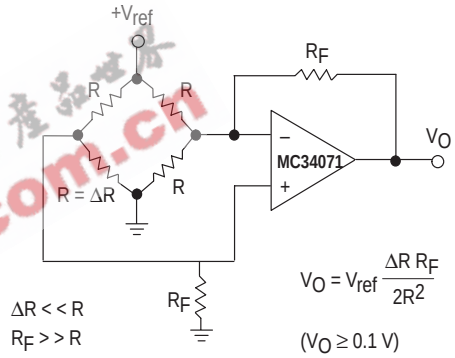


Figure 53. Low Voltage Peak Detector

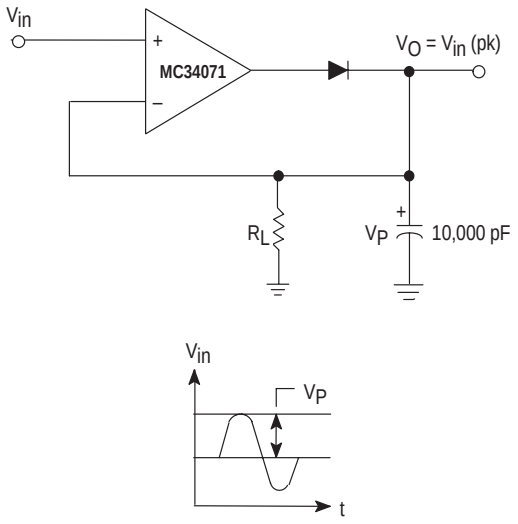
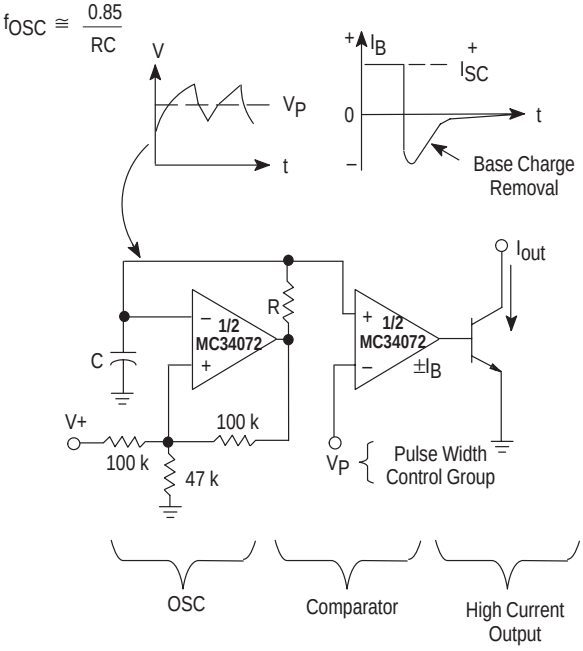


Figure 54. High Frequency Pulse Width Modulation



GENERAL ADDITIONAL APPLICATIONS INFORMATION V_S = ±15.0 V

Figure 55. Second Order Low–Pass Active Filter

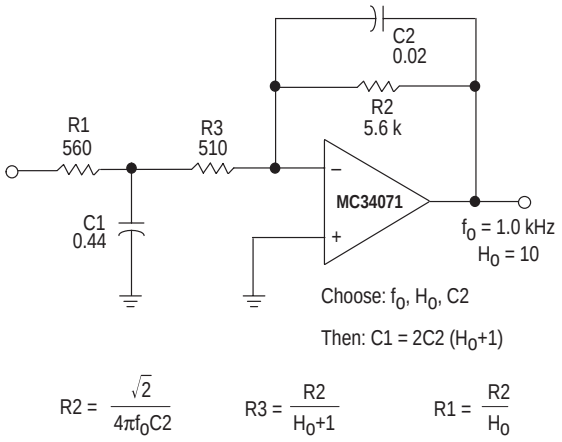


Figure 56. Second Order High–Pass Active Filter

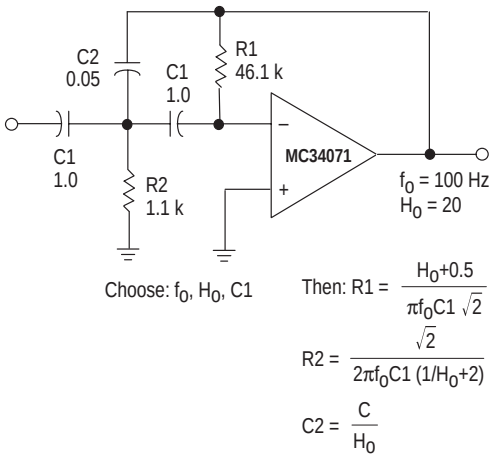


Figure 57. Fast Settling Inverter

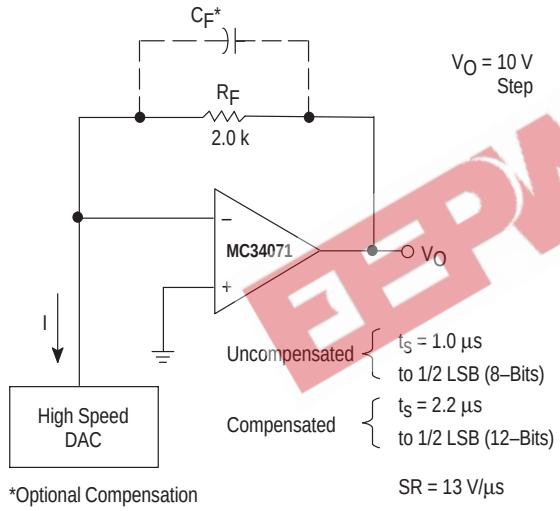


Figure 58. Basic Inverting Amplifier

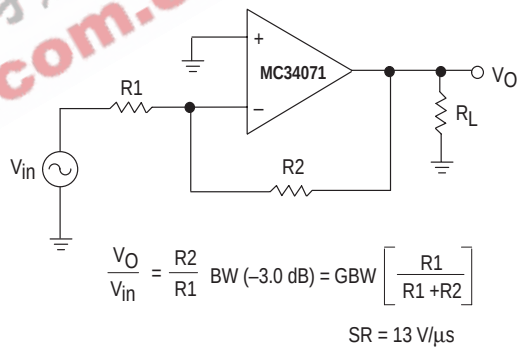


Figure 59. Basic Noninverting Amplifier

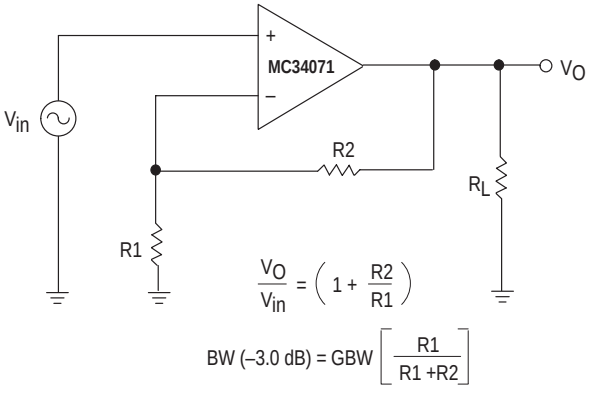


Figure 60. Unity Gain Buffer (A_V = +1.0)

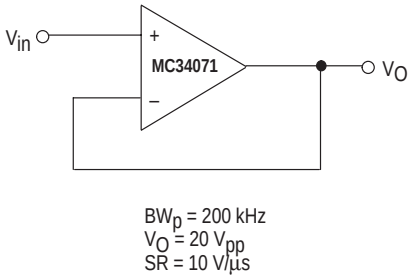


Figure 61. High Impedance Differential Amplifier

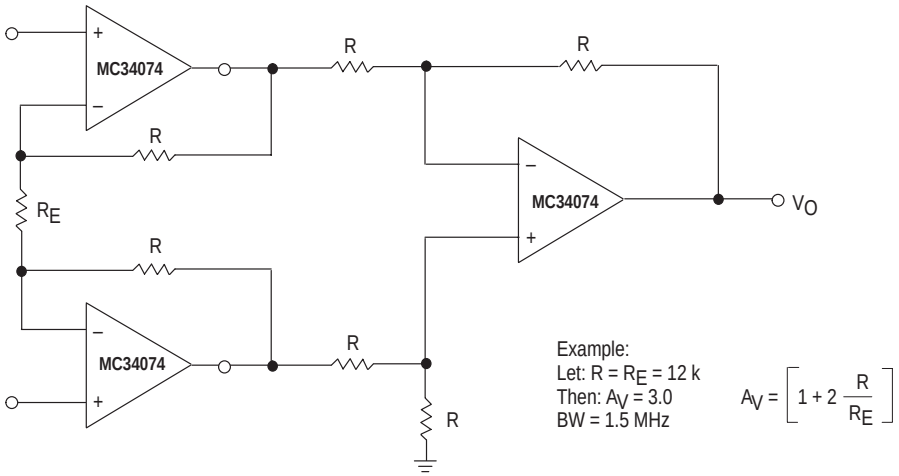
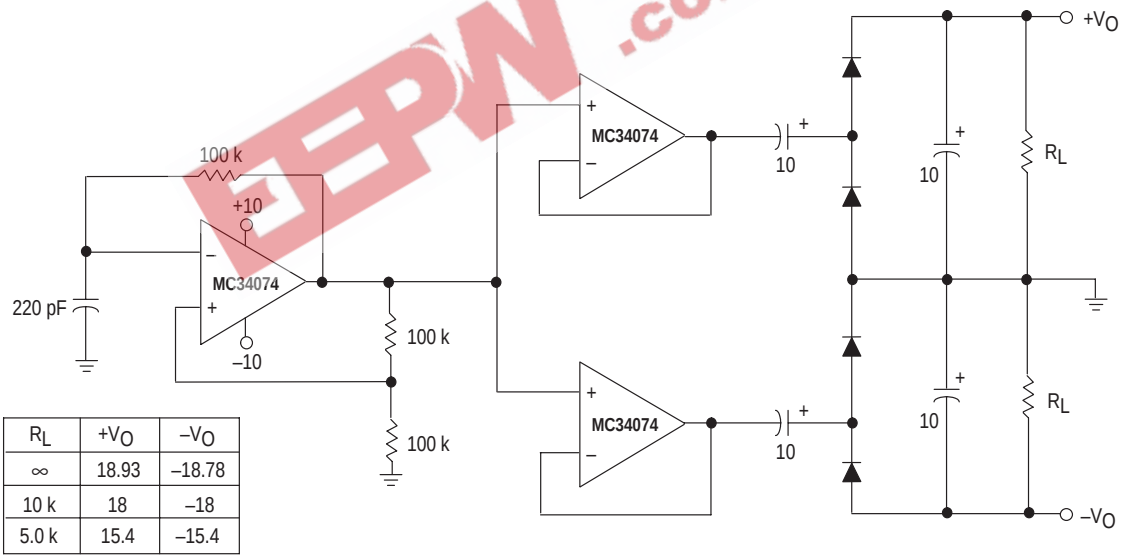


Figure 62. Dual Voltage Doubler



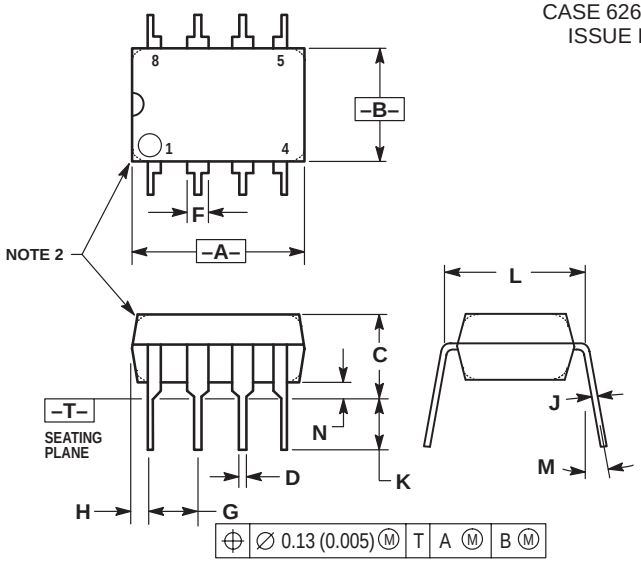
R_L	$+V_O$	$–V_O$
∞	18.93	–18.78
10 k	18	–18
5.0 k	15.4	–15.4

ORDERING INFORMATION

Op Amp Function	Device	Operating Temperature Range	Package	Shipping
Single	MC34071P, MC34071AP MC34071D, MC34071AD MC34071DR2, MC34071ADR2	T_A = 0° to +70°C	DIP–8 SO–8 SO–8 / Tape & Reel	50 Units / Rail 98 Units / Rail 2500 Units / Tape & Reel
	MC33071P, MC33071AP MC33071D, MC33071AD MC33071DR2, MC33071ADR2	T_A = –40° to +85°C	DIP–8 SO–8 SO–8 / Tape & Reel	50 Units / Rail 98 Units / Rail 2500 Units / Tape & Reel
Dual	MC34072P, MC34072AP MC34072D, MC34072AD MC34072DR2, MC34072ADR2	T_A = 0° to +70°C	DIP–8 SO–8 SO–8 / Tape & Reel	50 Units / Rail 98 Units / Rail 2500 Units / Tape & Reel
	MC33072P, MC33072AP MC33072D, MC33072AD MC33072DR2, MC33072ADR2	T_A = –40° to +85°C	DIP–8 SO–8 SO–8 / Tape & Reel	50 Units / Rail 98 Units / Rail 2500 Units / Tape & Reel
	MC34072VD MC34072VDR2	T_A = –40° to +125°C	SO–8 SO–8 / Tape & Reel	98 Units / Rail 2500 Units / Tape & Reel
Quad	MC34074P, MC34074AP MC34074D, MC34074AD MC34074DR2, MC34074ADR2	T_A = 0° to +70°C	DIP–8 SO–8 SO–8 / Tape & Reel	50 Units / Rail 98 Units / Rail 2500 Units / Tape & Reel
	MC33074P, MC33074AP MC33074D, MC33074AD MC33074DR2, MC33074ADR2 MC33074DTB, MC33074ADTB MC33074DTBR2, MC33074ADTBR2	T_A = –40° to +85°C	DIP–8 SO–8 SO–8 / Tape & Reel TSSOP–14 TSSOP–14 / Tape & Reel	50 Units / Rail 98 Units / Rail 2500 Units / Tape & Reel 96 Units / Rail 2500 Units / Tape & Reel
	MC34074VD MC34074VDR2	T_A = –40° to +125°C	SO–8 SO–8 / Tape & Reel	98 Units / Rail 2500 Units / Tape & Reel

PACKAGE DIMENSIONS

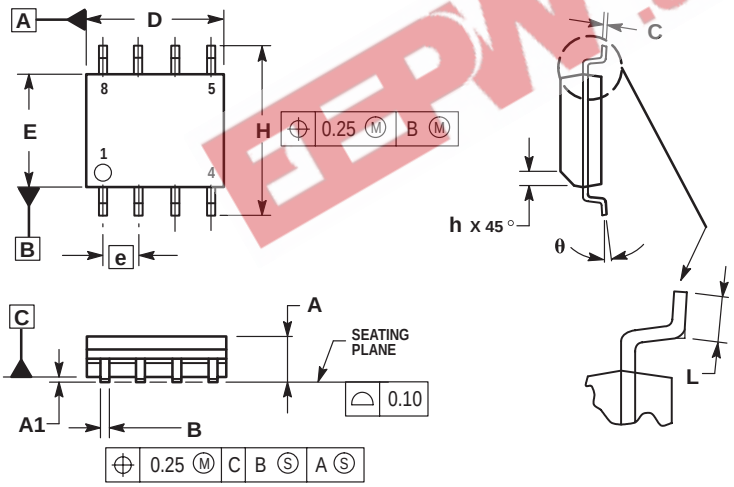
P SUFFIX
PLASTIC PACKAGE
CASE 626–05
ISSUE K



NOTES:
1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.40	10.16	0.370	0.400
B	6.10	6.60	0.240	0.260
C	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54 BSC		0.100 BSC	
H	0.76	1.27	0.030	0.050
J	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62 BSC		0.300 BSC	
M	—	10°	—	10°
N	0.76	1.01	0.030	0.040

D SUFFIX
(SO–8)
PLASTIC PACKAGE
CASE 751–05
ISSUE R

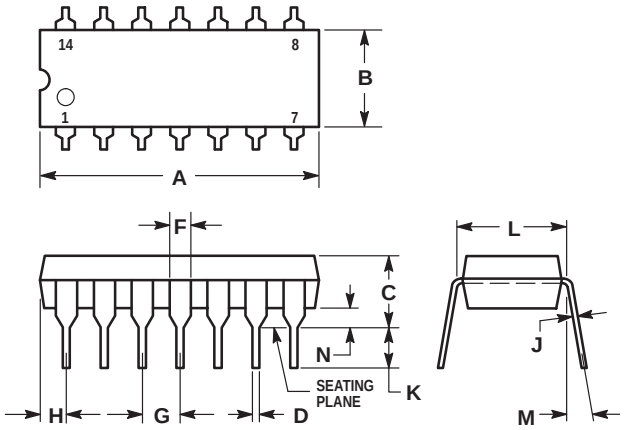


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSION D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS	
DIM	MIN	MAX
A	1.35	1.75
A1	0.10	0.25
B	0.35	0.49
C	0.18	0.25
D	4.80	5.00
E	3.80	4.00
e	1.27 BSC	
H	5.80	6.20
h	0.25	0.50
L	0.40	1.25
θ	0°	7°

PACKAGE DIMENSIONS

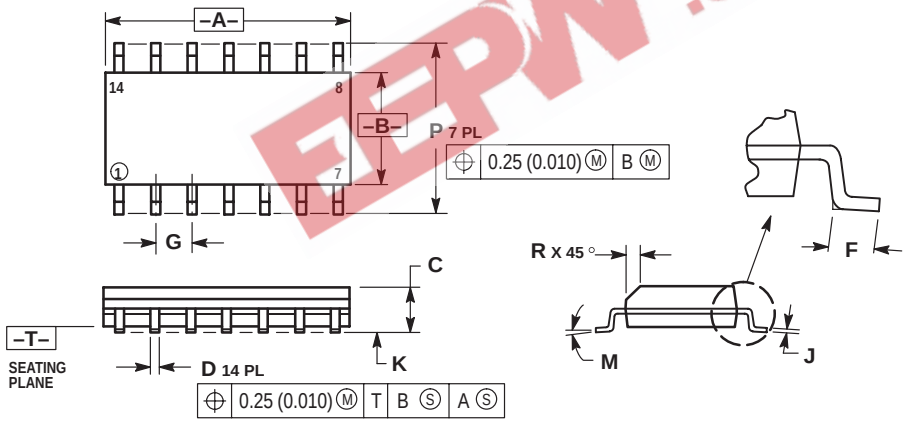
P SUFFIX
PLASTIC PACKAGE
CASE 646–06
ISSUE L



NOTES:
1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.
2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
3. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
4. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	19.56
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.300 BSC		7.62 BSC	
M	0 °	10 °	0 °	10 °
N	0.015	0.039	0.39	1.01

D SUFFIX
(SO–14)
PLASTIC PACKAGE
CASE 751A–03
ISSUE F

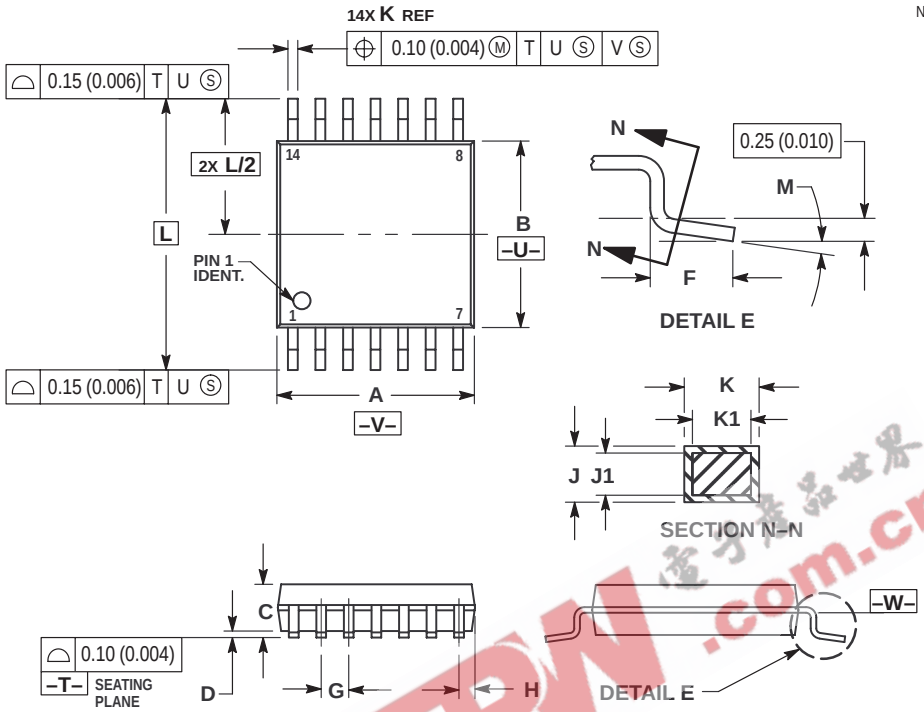


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

DTB SUFFIX
(TSSOP–14)
PLASTIC PACKAGE
CASE 948G–01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	—	1.20	—	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

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